



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of: Bruno GHYSELEN *et al.* Confirmation No.: 8095  
Application No.: 10/615,259 Group Art Unit: 2818  
Filing Date: July 9, 2003 Examiner: Thao P. Le  
For: PROCESS FOR TRANSFERRING A Attorney Docket No.: 4717-7500  
LAYER OF STRAINED  
SEMICONDUCTOR MATERIAL

**THIRD INFORMATION DISCLOSURE STATEMENT**

Commissioner for Patents  
P.O. Box 1450  
Alexandria, Virginia 22313-1450

Sir:

Pursuant to Applicant's duty of disclosure under 37 C.F.R. § 1.56, enclosed is a Form PTO-1449 listing four (4) references for the Examiner's review.

Copies of these references, B1 and C1-C3, are enclosed herewith.

It is respectfully requested that the references be made of record in this application by the Examiner's completion and return of the attached Form PTO-1449.

No fee is believed to be due for the submission of the these references. Should any fees be required, however, please charge such fees to Winston & Strawn LLP Deposit Account No. 50-1814.

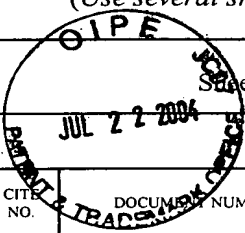
Respectfully submitted,

July 22, 2004  
Date

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E. Bradley Gould (Reg. No. 41,792)  
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**WINSTON & STRAWN LLP**  
**Customer No. 28765**

202-371-5771

<b>LIST OF REFERENCES CITED BY APPLICANT</b> <b>Form PTO-1449</b> <i>(Use several sheets if necessary)</i>				ATTY. DOCKET NO.:		APPLICATION NO.:	
				4717-7500		10/615,259	
 Sheet 1 of 1				APPLICANT:			
				Bruno GHYSELEN <i>et al.</i>			
				FILING DATE:		GROUP:	
				July 9, 2003		2818	
<b>U.S. PATENT DOCUMENTS</b>							
*EXAMINER INITIAL	CITE NO.	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
<b>FOREIGN PATENT DOCUMENTS</b>							
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
	B1	10-209453	08/1988	JP (Abstract)			
<b>OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, Etc.)</b>							
	C1	E.A. Fitzgerald et al. <i>Relaxed Ge<sub>x</sub>Si<sub>1-x</sub> structures for III-V integration with Si and high mobility two-dimensional electron gases in Si</i> ; <u>J.Vac.Sci.Technol</u> ; B 10(4), Jul/Aug 1992; pp. 1807-1819.					
	C2	R. Egloff et al. <i>Evaluation of Strain Sources in Bond and Etchback Silicon-on-Insulator</i> ; <u>Philips Journal of Research</u> ; Vol. 49, No. 1/2 1995; pp125-138.					
	C3	Cher Ming Tan et al. <i>Temperature and Stress Distribution in the SOI Structure During Fabrication</i> ; <u>ZIEEE Transactions on Semiconductor Manufacturing</u> , Vol. 16, No. 2, May 2003; pp. 314-317.					
EXAMINER				DATE CONSIDERED			
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with <b>MPEP 609</b> . Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							